

L Number	Hits	Search Text	DB	Time stamp
33	1	6335267.pn.	USPAT	2004/05/06 12:59
34	9083	(cmp or polish or polishing or planarize or planarizing) with (edge or bevel or peripheral)	USPAT; US-PGPUB; EPO; JPO	2004/05/06 13:47
35	2830	((cmp or polish or polishing or planarize or planarizing) with (edge or bevel or peripheral)) and (etch or etching)	USPAT; US-PGPUB; EPO; JPO	2004/05/06 13:48
36	2245	((((cmp or polish or polishing or planarize or planarizing) with (edge or bevel or peripheral)) and (etch or etching)) and @ay<=2001	USPAT; US-PGPUB; EPO; JPO	2004/05/06 13:48
37	1091	(((((cmp or polish or polishing or planarize or planarizing) with (edge or bevel or peripheral)) and (etch or etching)) and @ay<=2001) and (slurry or abrasive)	USPAT; US-PGPUB; EPO; JPO	2004/05/06 13:49
38	310	(((((cmp or polish or polishing or planarize or planarizing) with (edge or bevel or peripheral)) and (etch or etching)) and @ay<=2001) and (slurry or abrasive)) and (wire or wiring)	USPAT; US-PGPUB; EPO; JPO	2004/05/06 13:49
39	241	((((((cmp or polish or polishing or planarize or planarizing) with (edge or bevel or peripheral)) and (etch or etching)) and @ay<=2001) and (slurry or abrasive)) and (wire or wiring)) and @ay<=20010417	USPAT	2004/05/06 13:50
40	9	("5152857" "5254830" "5374564" "5494862" "5766065" "5928066" "5942445" "6312797" "6352927").PN.	USPAT	2004/05/06 13:51
41	8	("4393628" "4466218" "5899738" "6001447" "6045435" "6110021" "6121111" "6251215").PN.	USPAT	2004/05/06 14:21
42	1	"6091130".PN.	USPAT	2004/05/06 14:26
53	1	("6048763" "2002/0022936").PN.	USPAT	2004/05/06 15:07
54	11	("4193226" "4811522" "5421769" "5584746" "6010964" "6020262" "6171513" "6203408" "6340326" "6344414" "6368968").PN.	USPAT	2004/05/06 15:08
55	39545	(wire or wiring) same (pattern or patterning)	USPAT	2004/05/06 15:18
56	25648	(wire or wiring) with (pattern or patterning)	USPAT	2004/05/06 15:18
57	222	((cmp or polish or polishing or planarize or planarizing) with (edge or bevel or peripheral)) and ((wire or wiring) with (pattern or patterning))	USPAT	2004/05/06 15:18
58	207	((((cmp or polish or polishing or planarize or planarizing) with (edge or bevel or peripheral)) and ((wire or wiring) with (pattern or patterning))) and @ay<=2001	USPAT	2004/05/06 16:01
59	4209	wiring with interconnect	USPAT	2004/05/06 16:01
60	0	(wiring with interconnect) and semiconductor	USPAT	2004/05/06 16:01
61	2385	(wiring with interconnect) and semiconductor	USPAT	2004/05/06 16:01
62	2978	wiring near4 interconnect	USPAT	2004/05/06 16:01
63	1760	(wiring near4 interconnect) and semiconductor	USPAT	2004/05/06 16:02
64	583	((wiring near4 interconnect) and semiconductor) and polishing	USPAT	2004/05/06 16:02
65	398	((((wiring near4 interconnect) and semiconductor) and polishing) and copper	USPAT	2004/05/06 16:02

66	365	((((wiring near4 interconnect) and semiconductor) and polishing) and copper) and @ay<=2001	USPAT	2004/05/06 16:41
67	8	("6059889") or ("5901399") or ("5868857") or ("5976267") or ("5874778") or ("6334229") or ("6309981") or ("6267649").PN.	USPAT	2004/05/06 16:41
-	29472	(cmp or polish or polishing or planarize or planarizing) and (edge or pivot)	USPAT	2004/05/06 13:47
-	12603	((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor	USPAT	2004/05/05 11:09
-	6238	((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor and (etch or etching) and (mask or hard\$1mask)	USPAT	2004/05/05 11:09
-	1126	((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) same (edge or pivot))	USPAT	2004/05/05 11:11
-	485	((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) with (edge or pivot))	USPAT	2004/05/05 11:11
-	457	(((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) with (edge or pivot))) and @ay<=2001	USPAT	2004/05/05 11:12
-	284	(((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) same (edge or pivot))) and (slurry or abrasive)	USPAT	2004/05/05 11:12
-	145	(((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) with (edge or pivot))) and @ay<=2001) and (slurry or abrasive)	USPAT	2004/05/05 14:48
-	9	("5233218" "5258323" "5340435" "5494849" "5719426" "5973365" "5982003" "6118152" "6294478").PN.	USPAT	2004/05/05 11:40
-	3	((("6663468") or ("6596087") or ("6563172"))).PN.	USPAT	2004/05/05 12:57
-	1	("6379782").PN.	USPAT	2004/05/05 14:38
-	1	"6091130".PN.	USPAT	2004/05/05 12:57
-	61	Iguchi-Manabu.in.	USPAT; JPO; DERWENT; IBM TDB	2004/05/05 14:38
-	19	Iguchi-Manabu.in. and semiconductor	USPAT; JPO; DERWENT; IBM TDB	2004/05/05 14:38
-	1	"6091130".PN.	USPAT	2004/05/05 14:41

	139	(((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) same (edge or pivot))) and (slurry or abrasive)) not (((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) with (edge or pivot))) and @ay<=2001) and (slurry or abrasive))	USPAT	2004/05/05 15:20
	10	("5409569" "6136708" "6162301" "6165956" "6261849" "6287477" "6294027" "6303551" "6322598" "6387190" "2001/0029104").PN.	USPAT	2004/05/05 15:01
	1	Yoshihisa-Matsubara.in.	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/05/05 15:21
	103	Matsubara-Yoshihisa.in.	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/05/05 15:24
	99	Matsubara-Yoshihisa.in. and semiconductor	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/05/05 15:22
	20	(Matsubara-Yoshihisa.in. and semiconductor) and polishing	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/05/05 15:22
	22	Takewaki-Toshiyuki.in.	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/05/05 15:24
	4196	(cmp or polish or polishing or planarize or planarizing) with (edge or bevel\$3)	USPAT	2004/05/05 15:42
	1887	((cmp or polish or polishing or planarize or planarizing) with (edge or bevel\$3)) and semiconductor and @ay<=2001	USPAT	2004/05/05 15:34
	1217	((((cmp or polish or polishing or planarize or planarizing) with (edge or bevel\$3)) and semiconductor and @ay<=2001) and (slurry or abrasive))	USPAT	2004/05/05 15:35
	178	((((cmp or polish or polishing or planarize or planarizing) with (edge or bevel\$3)) and semiconductor and @ay<=2001) and (slurry or abrasive)) and (mask or hard\$1mask)	USPAT	2004/05/05 15:35

	176	(((((cmp or polish or polishing or planarize or planarizing) with (edge or bevel\$3)) and semiconductor and @ay<=2001) and (slurry or abrasive)) and (mask or hard\$1mask)) not (((((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) same (edge or pivot))) and (slurry or abrasive)) not (((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) with (edge or pivot))) and @ay<=2001) and (slurry or abrasive))) or Matsubara-Yoshihisa.in.)	USPAT	2004/05/05 15:35
-	1424	(cmp or polish or polishing or planarize or planarizing) and (chamfer\$3)	USPAT	2004/05/05 15:42
-	1428	(cmp or polish or polishing or planarize or planarizing) and (chamfer\$4)	USPAT	2004/05/05 15:42
-	428	((cmp or polish or polishing or planarize or planarizing) and (chamfer\$4)) and semiconductor	USPAT	2004/05/05 15:42
-	301	((((cmp or polish or polishing or planarize or planarizing) and (chamfer\$4)) and semiconductor) and (etch or etching)	USPAT	2004/05/05 15:42
-	281	((((cmp or polish or polishing or planarize or planarizing) and (chamfer\$4)) and semiconductor) and (etch or etching)) and @ay<=2001	USPAT	2004/05/05 15:42
-	265	(((((cmp or polish or polishing or planarize or planarizing) and (chamfer\$4)) and semiconductor) and (etch or etching)) and @ay<=2001) not (((((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) same (edge or pivot))) and (slurry or abrasive)) not (((((((cmp or polish or polishing or planarize or planarizing) and (edge or pivot)) and semiconductor) and (etch or etching) and (mask or hard\$1mask)) and ((cmp or polish or polishing or planarize or planarizing) with (edge or pivot))) and @ay<=2001) and (slurry or abrasive))) or Matsubara-Yoshihisa.in. and semiconductor) or (((((cmp or polish or polishing or planarize or planarizing) with (edge or bevel\$3)) and semiconductor and @ay<=2001) and (slurry or abrasive)) and (mask or hard\$1mask)))	USPAT	2004/05/05 15:43
-	9	("5152857" "5254830" "5374564" "5494862" "5766065" "5928066" "5942445" "6312797" "6352927").PN.	USPAT	2004/05/05 15:45
-	17	("4294651" "4372803" "4940510" "5233218" "5389551" "5426073" "5445706" "5449532" "5622875" "5893982" "5945351" "6033997" "6080675" "6099748" "6150969" "6294469" "6335267" "2001/0014570" "2001/0039101" "2002/0004305").PN.	USPAT	2004/05/05 15:48